Cancel C1

neutralization of the electrons held by the trap level by injecting holes generated in the vicinity of the drain region.

- Please replace the paragraph at page 13, lines 16-29, with the following amended text:

C2

On the other hand, the erasing operation is that an electric field is applied to between, e.g., the drain region 9 and the control gate 6, and the electrons trapped by the interface level within the insulating layer 20 are pulled to the drain region 9. Alternatively, considering that the electrons can not easily be released only by the electric field, an electron accumulated state is neutralized by injecting holes. To be specific, the source region 8 is grounded, the control gate 6 is given a negative potential, and the drain region 9 is given a positive high potential, respectively. Band-to-band tunneling is thereby induced by the drain junction, and the generated holes are injected into the insulating layer 20. with this operation, the erasing efficiency becomes by far higher than in the case of releasing the electrons by the electric field.

IN THE CLAIMS:

- Please cancel claims 1, 3, and 5.

- Please replace the text of claims 2, 4, and 6 with the following amended text:

C3

2. (Twice Amended) The non-volatile semiconductor memory according to claim 19, wherein an impurity dose quantity of said source region is larger than an impurity dose quantity of said drain region.